# **UB-Suffix Series CMOS Gates**

The UB Series logic gates are constructed with P and N channel enhancement mode devices in a single monolithic structure (Complementary MOS). Their primary use is where low power dissipation and/or high noise immunity is desired. The UB set of CMOS gates are inverting non–buffered functions.

- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Linear and Oscillator Applications
- Capable of Driving Two Low–power TTL Loads or One Low–power Schottky TTL Load Over the Rated Temperature Range
- Double Diode Protection on All Inputs
- Pin–for–Pin Replacements for Corresponding CD4000 Series UB Suffix Devices

## MAXIMUM RATINGS (Voltages Referenced to V<sub>SS</sub>) (Note 1.)

Symbol	Parameter	Value	Unit
V <sub>DD</sub>	DC Supply Voltage Range	-0.5 to +18.0	V
V <sub>in</sub> , V <sub>out</sub>	Input or Output Voltage Range (DC or Transient)	-0.5 to V <sub>DD</sub> + 0.5	V
I <sub>in</sub> , I <sub>out</sub>	Input or Output Current (DC or Transient) per Pin	±10	mA
P <sub>D</sub>	Power Dissipation, per Package (Note 2.)	500	mW
T <sub>A</sub>	Ambient Temperature Range	-55 to +125	°C
T <sub>stg</sub>	Storage Temperature Range	-65 to +150	°C
TL	Lead Temperature (8–Second Soldering)	260	°C

- Maximum Ratings are those values beyond which damage to the device may occur.
- Temperature Derating: Plastic "P and D/DW" Packages: – 7.0 mW/°C From 65°C To 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range  $V_{SS} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either  $V_{SS}$  or  $V_{DD}$ ). Unused outputs must be left open.



## ON Semiconductor

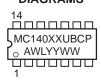
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MC14001UB
Quad 2-Input NOR Gate
MC14011UB
Quad 2-Input NAND Gate

# MARKING DIAGRAMS

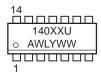


PDIP-14 P SUFFIX CASE 646





SOIC-14 D SUFFIX CASE 751A



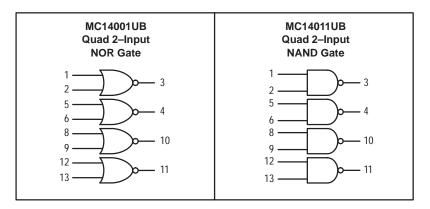
XX = Specific Device Code A = Assembly Location

WL or L = Wafer Lot YY or Y = Year WW or W = Work Week

## ORDERING INFORMATION

Device	Package	Shipping		
MC14001UBCP	PDIP-14	2000/Box		
MC14001UBD	SOIC-14	55/Rail		
MC14001UBDR2	SOIC-14	2500/Tape & Reel		
MC14011UBCP	PDIP-14	2000/Box		
MC14011UBD	SOIC-14	55/Rail		
MC14011UBDR2	SOIC-14	2500/Tape & Reel		

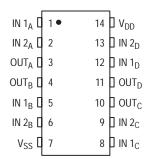
# **LOGIC DIAGRAMS**



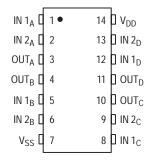
 $V_{DD}$  = PIN 14  $V_{SS}$  = PIN 7 FOR ALL DEVICES

# **PIN ASSIGNMENTS**

# MC14001UB Quad 2-Input NOR Gate



# MC14011UB Quad 2-Input NAND Gate



# **ELECTRICAL CHARACTERISTICS** (Voltages Referenced to V<sub>SS</sub>)

			V <sub>DD</sub>	_ 55°C		25°C		125°C			
Characterist	ic	Symbol	Vdc	Min	Max	Min	Тур (3.)	Max	Min	Max	Unit
Output Voltage V <sub>in</sub> = V <sub>DD</sub> or 0	"0" Level	V <sub>OL</sub>	5.0 10 15	_ _	0.05 0.05 0.05	_ _ _	0 0 0	0.05 0.05 0.05	_ _ _	0.05 0.05 0.05	Vdc
$V_{in} = 0 \text{ or } V_{DD}$	"1" Level	V <sub>OH</sub>	5.0 10 15	4.95 9.95 14.95	_ _ _	4.95 9.95 14.95	5.0 10 15	_ _ _	4.95 9.95 14.95	_ _ _	Vdc
Input Voltage $(V_O = 4.5 \text{ Vdc})$ $(V_O = 9.0 \text{ Vdc})$ $(V_O = 13.5 \text{ Vdc})$	"0" Level	V <sub>IL</sub>	5.0 10 15		1.0 2.0 2.5		2.25 4.50 6.75	1.0 2.0 2.5		1.0 2.0 2.5	Vdc
$(V_O = 0.5 \text{ Vdc})$ $(V_O = 1.0 \text{ Vdc})$ $(V_O = 1.5 \text{ Vdc})$	"1" Level	I <sub>IH</sub>	5.0 10 15	4.0 8.0 12.5	_ _ _	4.0 8.0 12.5	2.75 5.50 8.25	_ _ _	4.0 8.0 12.5	_ _ _	Vdc
Output Drive Current (V <sub>OH</sub> = 2.5 Vdc) (V <sub>OH</sub> = 4.6 Vdc) (V <sub>OH</sub> = 9.5 Vdc) (V <sub>OH</sub> = 13.5 Vdc)	Source	I <sub>OH</sub>	5.0 5.0 10 15	- 1.2 - 0.25 - 0.62 - 1.8	_ _ _ _	- 1.0 - 0.2 - 0.5 - 1.5	- 1.7 - 0.36 - 0.9 - 3.5	_ _ _ _	- 0.7 - 0.14 - 0.35 - 1.1	_ _ _ _	mAdc
$(V_{OL} = 0.4 \text{ Vdc})$ $(V_{OL} = 0.5 \text{ Vdc})$ $(V_{OL} = 1.5 \text{ Vdc})$	Sink	I <sub>OL</sub>	5.0 10 15	0.64 1.6 4.2	_ _ _	0.51 1.3 3.4	0.88 2.25 8.8	_ _ _	0.36 0.9 2.4	_ _ _	mAdc
Input Current		I <sub>in</sub>	15	_	± 0.1	_	±0.00001	± 0.1	_	± 1.0	μAdc
Input Capacitance (V <sub>in</sub> = 0)		C <sub>in</sub>	_	_	_	_	5.0	7.5	_	_	pF
Quiescent Current (Per Package)		I <sub>DD</sub>	5.0 10 15	_ _ _	0.25 0.5 1.0	_ _ _	0.0005 0.0010 0.0015	0.25 0.5 1.0	_ _ _	7.5 15 30	μAdc
Total Supply Current $(4.)$ (5.) I <sub>T</sub> (Dynamic plus Quiescent, Per Gate C <sub>L</sub> = 50 pF)		Ι <sub>Τ</sub>	5.0 10 15			$I_{T} = (0.0)$	3 μΑ/kHz) f - 6 μΑ/kHz) f - 8 μΑ/kHz) f -	· I <sub>DD</sub> /N			μAdc

Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.
 The formulas given are for the typical characteristics only at 25°C.
 To calculate total supply current at loads other than 50 pF:

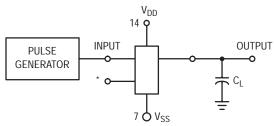
$$I_T(C_L) = I_T(50 \text{ pF}) + (C_L - 50) \text{ Vfk}$$

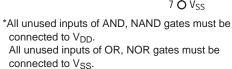
where:  $I_T$  is in  $\mu H$  (per package),  $C_L$  in pF,  $V = (V_{DD} - V_{SS})$  in volts, f in kHz is input frequency, and k = 0.001 x the number of exercised gates per package.

# SWITCHING CHARACTERISTICS (6.) ( $C_L = 50 \text{ pF}, T_A = 25^{\circ}\text{C}$ )

Characteristic	Symbol	V <sub>DD</sub> Vdc	Min	Typ <sup>(7.)</sup>	Max	Unit
Output Rise Time $t_{TLH} = (3.0 \text{ ns/pF}) C_L + 30 \text{ ns} \\ t_{TLH} = (1.5 \text{ ns/pF}) C_L + 15 \text{ ns} \\ t_{TLH} = (1.1 \text{ ns/pF}) C_L + 10 \text{ ns}$	t <sub>TLH</sub>	5.0 10 15	_ _ _	180 90 65	360 180 130	ns
Output Fall Time $t_{THL} = (1.5 \text{ ns/pF}) C_L + 25 \text{ ns} \\ t_{THL} = (0.75 \text{ ns/pF}) C_L + 12.5 \text{ ns} \\ t_{THL} = (0.55 \text{ ns/pF}) C_L + 9.5 \text{ ns}$	t <sub>THL</sub>	5.0 10 15	_ _ _	100 50 40	200 100 80	ns
Propagation Delay Time $t_{PLH},t_{PHL}=(1.7\;\text{ns/pF})\;C_L+30\;\text{ns}$ $t_{PLH},t_{PHL}=(0.66\;\text{ns/pF})\;C_L+22\;\text{ns}$ $t_{PLH},t_{PHL}=(0.50\;\text{ns/pF})\;C_L+15\;\text{ns}$	t <sub>PLH</sub> , t <sub>PHL</sub>	5.0 10 15	_ _ _	90 50 40	180 100 80	ns

<sup>6.</sup> The formulas given are for the typical characteristics only at  $25\,^{\circ}$ C.





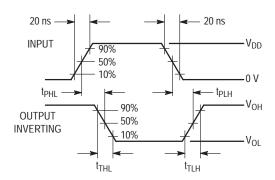


Figure 1. Switching Time Test Circuit and Waveforms

<sup>7.</sup> Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

# MC14001UB CIRCUIT SCHEMATIC

# 1 0 0 14 0 10 0 9 9 9 9 13 5 0 12 V<sub>SS</sub> 0 11 V<sub>SS</sub> 0 11

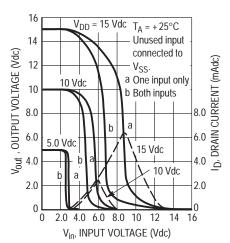
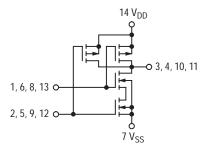


Figure 2. Typical Voltage and Current Transfer Characteristics

# MC14011UB CIRCUIT SCHEMATIC (1/4 of Device Shown)



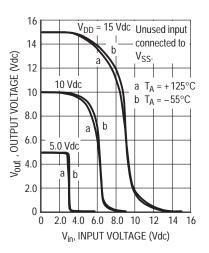


Figure 3. Typical Voltage Transfer Characteristics versus Temperature

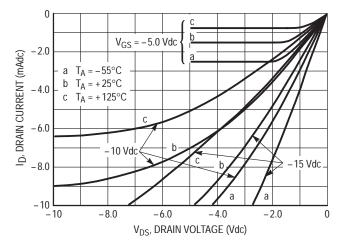


Figure 4. Typical Output Source Characteristics

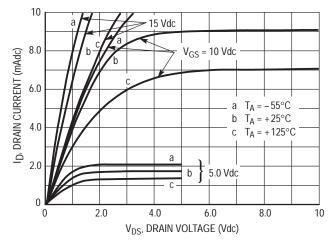
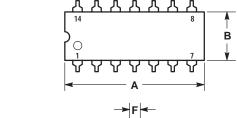
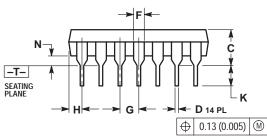


Figure 5. Typical Output Sink Characteristics

# **PACKAGE DIMENSIONS**

# **P SUFFIX** PLASTIC DIP PACKAGE CASE 646-06 ISSUE M





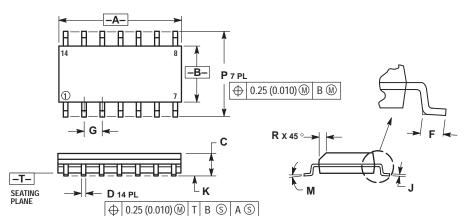


- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
  4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
  5. ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.715	0.770	18.16	18.80
В	0.240	0.260	6.10	6.60
С	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100 BSC		2.54 BSC	
Н	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.290	0.310	7.37	7.87
М		10°		10°
N	0.015	0.039	0.38	1 01

# **PACKAGE DIMENSIONS**

## **D SUFFIX** PLASTIC SOIC PACKAGE CASE 751A-03 ISSUE F



## NOTES:

- OTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI
  Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSIONS A AND B DO NOT INCLUDE
  MOLD PROTRUSION.
  4. MAXIMUM MOLD PROTRUSION 0.15 (0.006)
- 4. MAXIMUM MOLLD PROTRUSION 0.19 (0.000) PER SIDE.
  5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	METERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	8.55	8.75	0.337	0.344	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0 °	7°	0 °	7°	
Р	5.80	6.20	0.228	0.244	
R	0.25	0.50	0.010	0.019	

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